All data in this excel file refer to the paper published in JVST-B of DOI: 10.1116/1.4974219.

The measured devices have structures S1-S6 as illustrated in the paper Table 1.

For all figures, the current density (J) is the measured current (I) in Amperes divided by the device area (100 μm×100 μm).

T is the temperature in Kelvin [K]. The columns under 300K refer to IV measurements at 300K. Same for other temperatures: 325K, 350K, and 375K.

The activation energy (Ea) (Fig.6) is extracted from the linear fitting of the Arrhenius plots (Fig.5), where I ∝ V×exp[-Ea/(kT)].

The asymmetry Fig.7 (b), non-linearity Fig.7 (c) and dynamic resistance Fig.7 (d) are all defined with their equations in the paper in the introduction section.